A theoretical study of electron drift mobility anisotropy in n-type 4H- and 6H-SiC

Velmre, Enn; **Udal, Andres** Abstracts of International Conference on Silicon Carbide and Related Materials: ICSCRM'99: October 10-15, 1999, Research Triangle Park, North-Carolina, USA 1999 / paper no 395, 2 p

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